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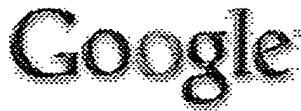
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<u>L3</u>	CMOS and (((NMOS near5 PMOS)near5 height)same (equal\$3 near3 mobility))	0	<u>L3</u>
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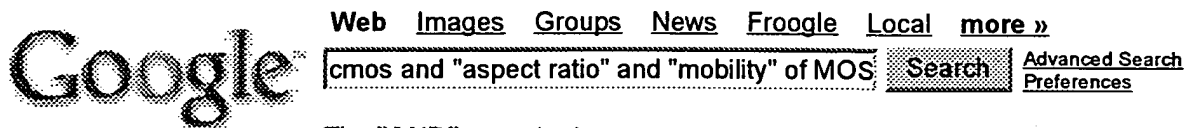
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<u>L7</u>	L5	0	<u>L7</u>
<u>L6</u>	L5	0	<u>L6</u>
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<u>L5</u>	L4	0	<u>L5</u>
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<u>L4</u>	near3 mobility))	0	<u>L4</u>
<u>L3</u>	CMOS and (((NMOS near5 PMOS)near5 height)same (equal\$3 near3 mobility))	0	<u>L3</u>
<u>L2</u>	CMOS and (((NMOSFET near5 PMOSFET)near5 height)same (equal\$3 near3 mobility))	0	<u>L2</u>
<u>L1</u>	CMOS and (height same (equal\$3 near3 mobility))	0	<u>L1</u>

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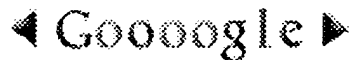
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